

Low Capacitance / Low Forward Resistance PIN Diodes

RN142G/S

Application
High-frequency switching

- Features**
- Sub-miniature mold type (VMD2/EMD2)
 - Low capacity with very low high-frequency forward resistance

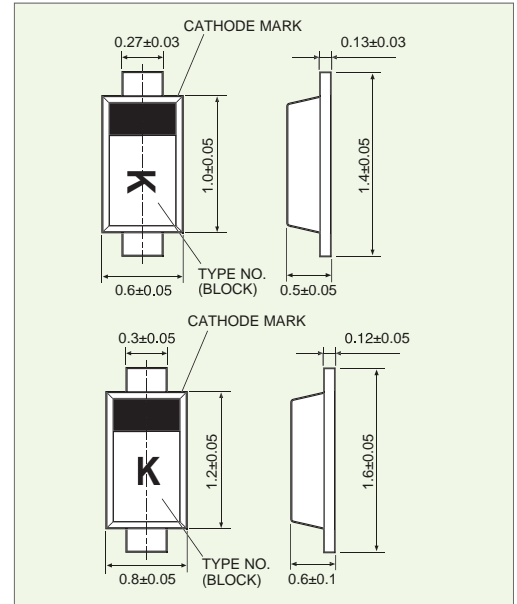
Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
DC reverse voltage	V _R	60	V
DC forward current	I _F	100	mA
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~+150	°C

Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	Standard
Forward voltage	V _F	I _F =10mA	1.0V MAX.
Reverse current	I _R	V _R =60V	0.1μA MAX.
Capacity between pins	C _t	V _R =1.0V f=1.0MHz	0.45pFMAX.
High-frequency resistance	R _f	I _F =3mA f=100MHz	3.0 MAX.
		I _F =10mA f=100MHz	2.0 MAX.

External Dimensions (Unit: mm)



RN152G

Application
High-frequency switching

- Features**
- Sub-miniature mold type (VMD2)
 - Low capacity with very low high-frequency forward resistance

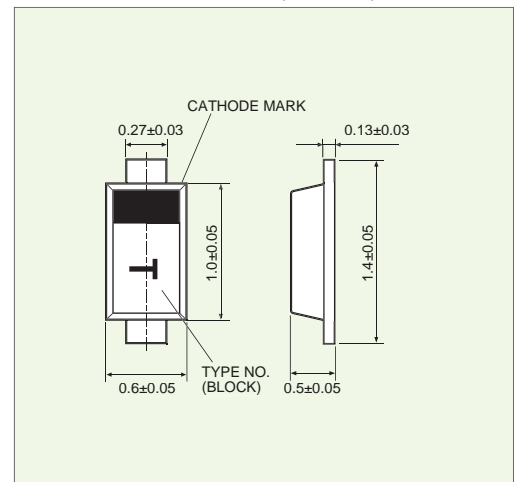
Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
DC reverse voltage	V _R	30	V
DC forward current	I _F	100	mA
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~+150	°C

Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	Standard
Forward voltage	V _F	I _F =10mA	1.0V MAX.
Reverse current	I _R	V _R =30V	0.1μA MAX.
Capacity between pins	C _t	V _R =1.0V f=1.0MHz	0.15pFMIN. 0.45pFMAX.
High-frequency resistance	R _f	I _F =1mA f=100MHz	4.8 MAX.
		I _F =10mA f=100MHz	1.8 MAX.

External Dimensions (Unit: mm)



RN242CS

Application
High-frequency switching

- Features**
- Sub-miniature mold type (VMD2)
 - Low capacity with very low high-frequency forward resistance

Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
DC reverse voltage	V _R	30	V
DC forward current	I _F	100	mA
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~+150	°C

Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	Standard
Forward voltage	V _F	I _F =10mA	1.0V MAX.
Reverse current	I _R	V _R =30V	0.1μA MAX.
Capacity between pins	C _t	V _R =1.0V f=1.0MHz	0.35pFMAX.
High-frequency resistance	R _f	I _F =3mA f=100MHz	3.0 MAX.
		I _F =10mA f=100MHz	1.5 MAX.

External Dimensions (Unit: mm)

